

(19)
(12)

(KR)
(A)

(51) . Int. Cl.⁷
H04B 1/06
H04B 1/38

(11) 10-2004-0105835
(43) 2004 12 16

(21)	10-2004-7015618		
(22)	2004 10 01		
	2004 10 01		
(86)	PCT/US2003/010283	(87)	WO 2003/085850
(86)	2003 04 03	(87)	2003 10 16

(30)	60/370,016	2002 04 03	(US)
------	------------	------------	------

(71)	92648	46
------	-------	----

(72)	,	46228	3903
------	---	-------	------

,	,	46240	9402
---	---	-------	------

,	,	46259	8767
---	---	-------	------

,	,	46060	121
---	---	-------	-----

,	,	46032	246
---	---	-------	-----

(74)

:

(54)

가

가

,
,

3

< >
2002 4 3 60/370,016 가 , 2002 5 20 60/381,859 가

< >

V_o LNB(86)
 13V (right hand circular polarization; PHCP) , 18V
 (left hand circular polarization; LHCP)

1 LNB(86) 13V 18V 가
 . LNB(86) IO 13V 18V

2 1 . () V_o IO 가
가 . 2 6

, , ,
(13 가) , (16 가) , (13 가) 18V가 22 가 , , ,

() 가 18V

< >

<	>						
3		(10)	(10)가	1		(LNB; 86)	
1	3	LNB(86)	.	(16)	V_o	(Q1)	(16)
(20)	(84)	V_o	.	V_IN	.	(Q1)	(16)
LNB	(7)	V_o	(53)	2-	V_o	(23c)	(Q1)
.	V_o	.	.	2	.	.	.

(22a) , V_O (22) , (22) AND TRUE 10V (23a) (23c) (22a) (41) (23)
 b) , (23b) , 18V V_O TRUE (23c) 가 13V (41) (23)
 o FALSE 가 V_O 18V V_O (LHCP) (10) 13V
 1 (RHCp) (85) 3 13V Muterspaug
 h Patent

, 3 LNB (10) V_{IN}
 (200) . 18 V_O (metal oxide semiconductor field effect transistor; MOSFET)(51) (23c)
 (301) (Q1) 22 V_{IN}, 13
 V_O , MOSFET(51) V_{IN} (21) 16 V_{IN}
 , (21) (21) MOSFET(51) (Q1)

. 가 , (10) 22 V_{IN} 18 V_O
 . , (10) 16 V_{IN} 13 V_O

1 LNB(86) LNB 13V 18V V_O 5V () () () LNB
 (5V) (6V) V_O 가 LNB(86) V_O 가 6 I_O 2
 , 3 (10) , V_O , V_O , I_O (16) (16) V_O 6 10 2 6

V_O 가 6V I_O 가 V_O 22 3 V_{IN} (Q1) (Q1)
 , (Q1) , (Q1) , V_O , (Q1)

, 3 AND (22) 4 (91) V_O 가 10V (23a) 가 LOW (22) V_O 가 (23a) 가 LOW
 (23) (23) (23b) (41) (41) (23b) (92)
 V_O 가 13V 13V

, 13V V_O (Q1) 가 13V V_O , MOSFET(51) (23b)
 (21) , (Q1) , V_O , V_{IN} (22a)

5 가 AND (23) , 3 (23a) (23)
 (41) , (22) (41) , 3 (23b) (53) LOW (23b), 5 (41) (111) (23)
 , 3 (112) (41) , (23a) 가 (41) , 5 (113) 13 (114) 가
 (10) , 5 (115) 13 (111) 가

3 (41) (116) LOW 3 HIGH (23a)
 5 V_o 가 18V 18 , HIGH (23b) (10) 가
 6 1 LNB(86) (10')
 3 6 ,
 6 (10') 가 ,
 , (310') (Q1') (Q1')
 (310') (51a') (51b') 3 6
 , ,
 , V_o 가 (301'), 22 13 13 (310') 13
 (310') 9 Ohm 가 , MOSFET(51') 2 13
 51) V_o 가 6 16 (310') 13 (21) MESFET(V
 o 가 , , , MOSFET(51') 가
 LNB 13 , 13 (Q1') (310') V_o 가

(57)

1.

1 가 , 2 가 1 ;
 1 1 , - 2 1 1 ;
 , 1 1 가 , 2 1 - , 2 1 ;
 , 2 , 2 가 , , ;

2.

1 , 1 , 2 , 1 2

3.

2 , ;

, 1 2 1 ,

, 2

4.

2 ,

, 2 1 , 1
2 , 1 2 , 2

5.

2 ,

6.

1 ,

2

7.

6 ,

1 2

8.

6 ,

1 2

9.

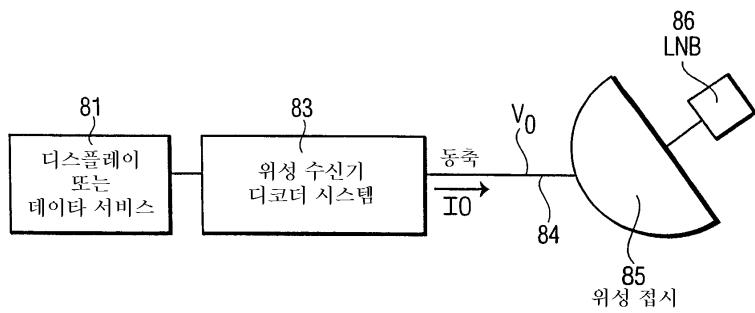
1 ,

2 ,

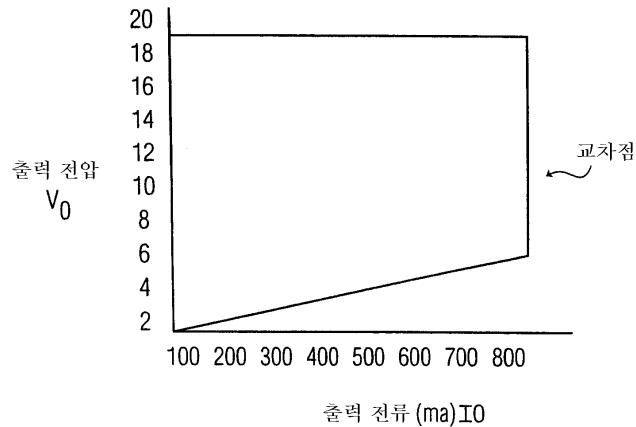
2

2 2 가 , ,
2 가 , ,

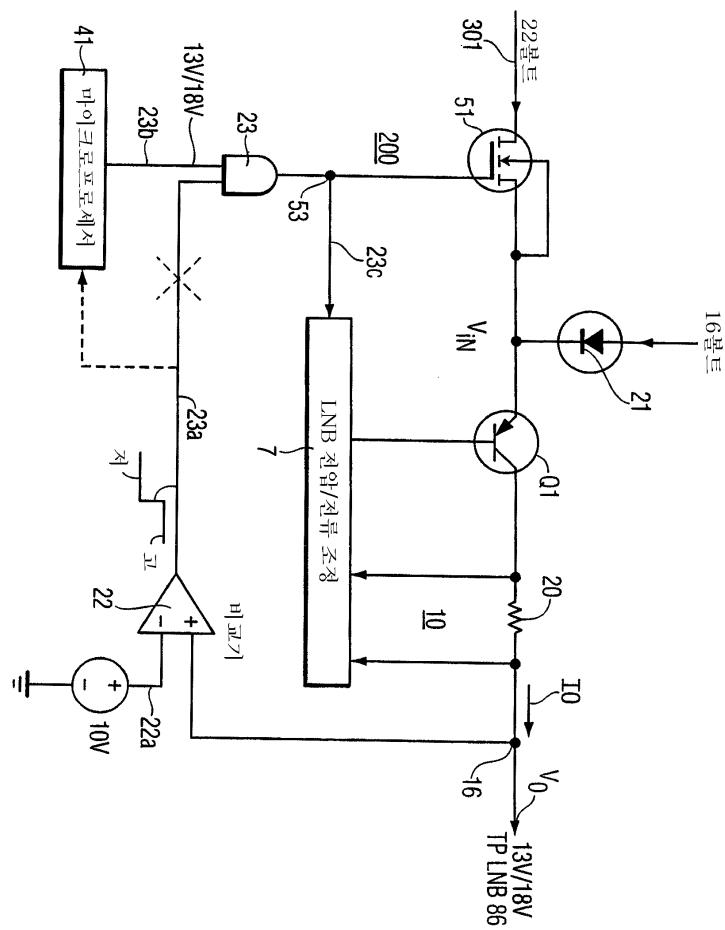
1



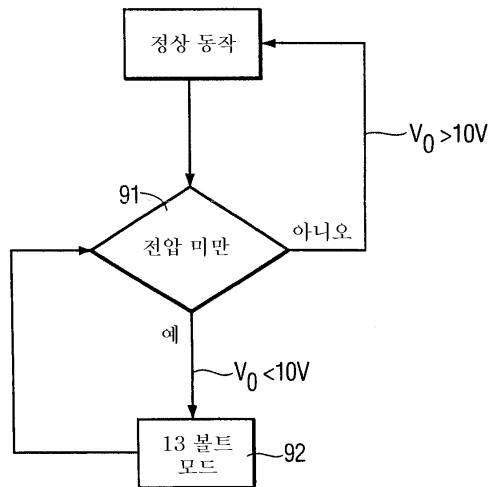
2



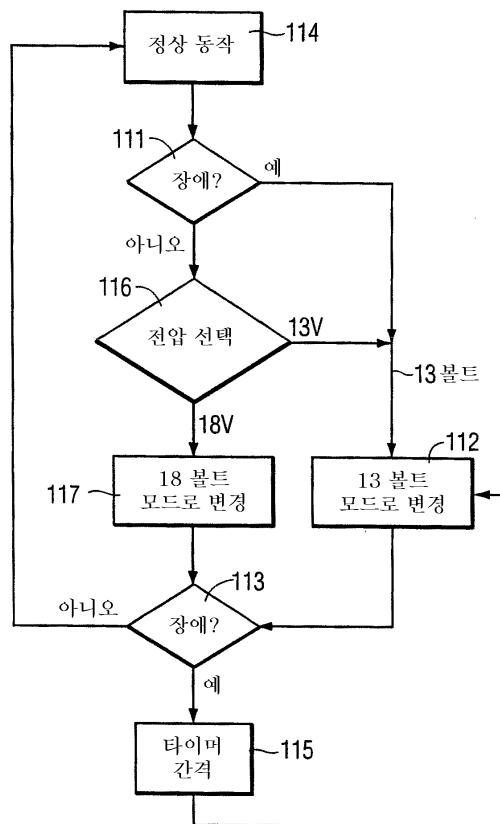
3



4



5



6

